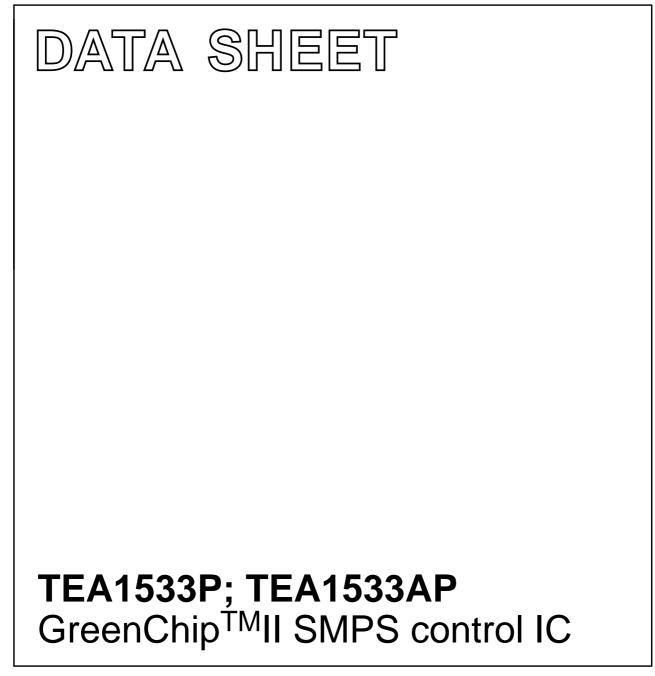
INTEGRATED CIRCUITS



Product specification Supersedes data of 2002 May 31 2002 Aug 23



### FEATURES

### **Distinctive features**

- Universal mains supply operation (70 to 276 V AC)
- High level of integration, giving a very low external component count.

### **Green features**

- Valley or zero voltage switching for minimum switching losses
- Efficient quasi-resonant operation at high power levels
- Frequency reduction at low power standby for improved system efficiency (<3 W)
- Cycle skipping mode at very low loads. P<sub>i</sub> <300 mW at no-load operation for a typical adapter application
- On-chip start-up current source.

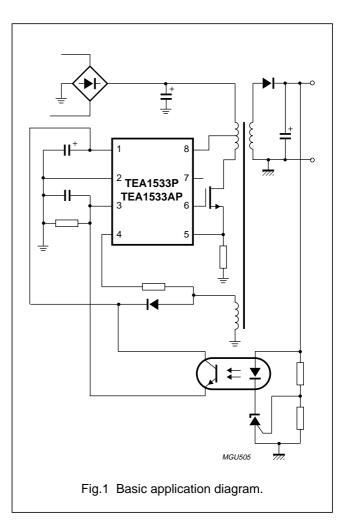
### **Protection features**

- · Safe restart mode for system fault conditions
- Continuous mode protection by means of demagnetization detection (zero switch-on current)
- Accurate and adjustable overvoltage protection (latched in TEA1533P, safe restart in TEA1533AP)
- Short winding protection
- Undervoltage protection (foldback during overload)
- Overtemperature protection (latched in TEA1533P, safe restart in TEA1533AP)
- Low and adjustable overcurrent protection trip level
- Soft (re)start
- Mains voltage-dependent operation enabling level.

### **APPLICATIONS**

Besides typical application areas, i.e. adapters and chargers, the device can be used in TV and monitor supplies and all applications that demand an efficient and cost-effective solution up to 250 W.

TEA1533P; TEA1533AP



### GENERAL DESCRIPTION

The GreenChip<sup>TM(1)</sup>II is the second generation of green Switched Mode Power Supply (SMPS) control ICs operating directly from the rectified universal mains. A high level of integration leads to a cost effective power supply with a very low number of external components.

The special built-in green functions allow the efficiency to be optimum at all power levels. This holds for quasi-resonant operation at high power levels, as well as fixed frequency operation with valley switching at medium power levels. At low power (standby) levels, the system operates at a reduced frequency and with valley detection.

(1) GreenChip is a trademark of Koninklijke Philips Electronics N.V.

### **ORDERING INFORMATION**

The proprietary high voltage BCD800 process makes direct start-up possible from the rectified mains voltage in an effective and green way. A second low voltage

TEA1533P; TEA1533AP

Highly efficient and reliable supplies can easily be designed using the GreenChipII control IC.

functions and control.

BICMOS IC is used for accurate, high-speed protection

TYPE NUMBER		PACKAGE					
ITPE NOWBER	NAME	DESCRIPTION	VERSION				
TEA1533P	DIP8	plastic dual in-line package; 8 leads (300 mil)	SOT97-1				
TEA1533AP							

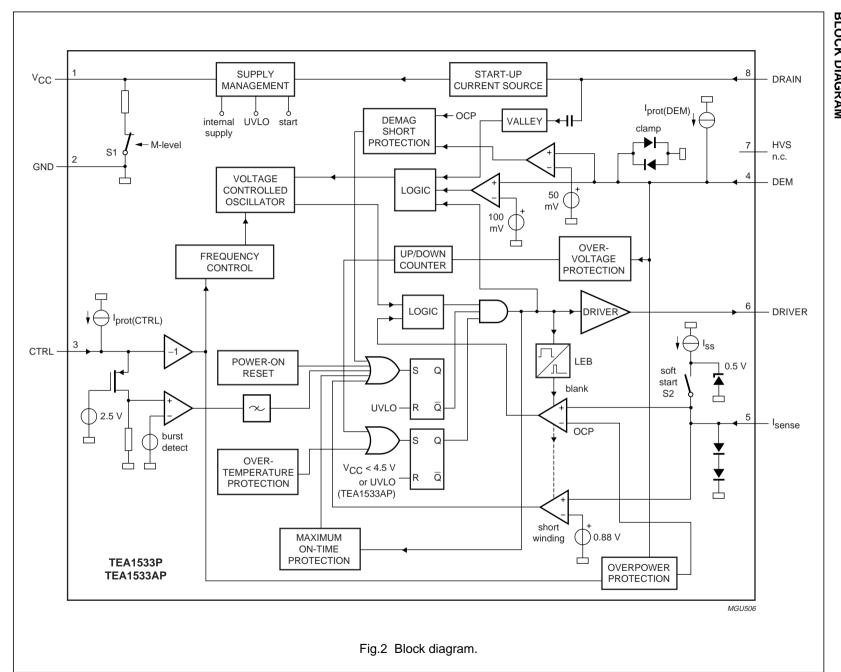
Philips Semiconductors

Product specification

# GreenChip<sup>TM</sup>II SMPS control IC

## TEA1533P; TEA1533AP

### **BLOCK DIAGRAM**



2002 Aug 23

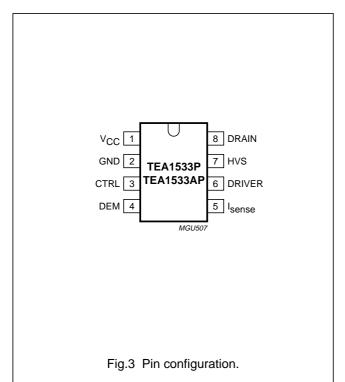
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### TEA1533P; TEA1533AP

### PINNING

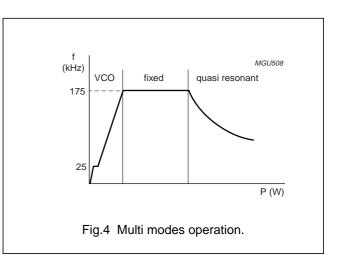
SYMBOL	PIN	DESCRIPTION
V <sub>CC</sub>	1	supply voltage
GND	2	ground
CTRL	3	control input
DEM	4	input from auxiliary winding for demagnetization timing, overvoltage and overpower protection
I <sub>sense</sub>	5	programmable current sense input
DRIVER	6	gate driver output
HVS	7	high voltage safety spacer, not connected
DRAIN	8	drain of external MOS switch, input for start-up current and valley sensing



### FUNCTIONAL DESCRIPTION

The TEA1533 is the controller of a compact flyback converter, and is situated at the primary side. An auxiliary winding of the transformer provides demagnetization detection and powers the IC after start-up.

The TEA1533 can operate in multi modes (see Fig.4).



The next converter stroke is started only after demagnetization of the transformer current (zero current switching), while the drain voltage has reached the lowest voltage to prevent switching losses (green function). The primary resonant circuit of the primary inductance and drain capacitor ensures this quasi-resonant operation. The design can be optimized in such a way that zero voltage switching can be reached over almost the universal mains range.

To prevent very high frequency operation at lower loads, the quasi-resonant operation changes smoothly in fixed frequency PWM control.

At very low power (standby) levels, the frequency is controlled down, via the VCO, to a minimum frequency of approximately 25 kHz.

### Start-up, mains enabling operation level and undervoltage lock-out

Initially, the IC is self supplying from the rectified mains voltage via pin DRAIN (see Figs 11 and 12). Supply capacitor  $C_{VCC}$  is charged by the internal start-up current source to approximately 4 V or higher, depending on the voltage on pin DRAIN.

TEA1533P; TEA1533AP

Once the drain voltage exceeds the M-level (mains-dependent operation-enabling level), the start-up current source will continue charging capacitor  $C_{VCC}$  (switch S1 will be opened); see Fig.2. The IC will activate the converter as soon as the voltage on pin  $V_{CC}$  passes the  $V_{CC(start)}$  level.

The IC supply is taken over by the auxiliary winding as soon as the output voltage reaches its intended level and the IC supply from the mains voltage is subsequently stopped for high efficiency operation (green function).

The moment the voltage on pin  $V_{CC}$  drops below the undervoltage lock-out level, the IC stops switching and enters a safe restart from the rectified mains voltage. Inhibiting the auxiliary supply by external means causes the converter to operate in a stable, well defined burst mode.

### Supply management

All (internal) reference voltages are derived from a temperature compensated, on-chip band gap circuit.

### **Current mode control**

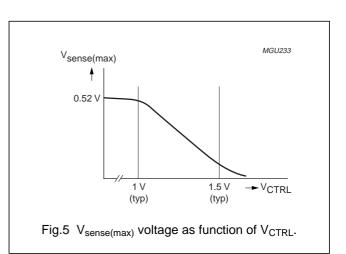
Current mode control is used for its good line regulation behaviour.

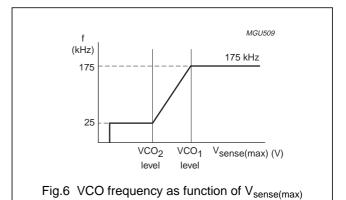
The 'on-time' is controlled by the internally inverted control voltage, which is compared with the primary current information. The primary current is sensed across an external resistor. The driver output is latched in the logic, preventing multiple switch-on.

The internal control voltage is inversely proportional to the external control pin voltage, with an offset of 1.5 V. This means that a voltage range from 1 to 1.5 V on pin CTRL will result in an internal control voltage range from 0.5 to 0 V (a high external control voltage results in a low duty cycle).

### Oscillator

The maximum fixed frequency of the oscillator is set by an internal current source and capacitor. The maximum frequency is reduced once the control voltage enters the VCO control window. Then, the maximum frequency changes linearly with the control voltage until the minimum frequency is reached (see Figs 5 and 6).





### Cycle skipping

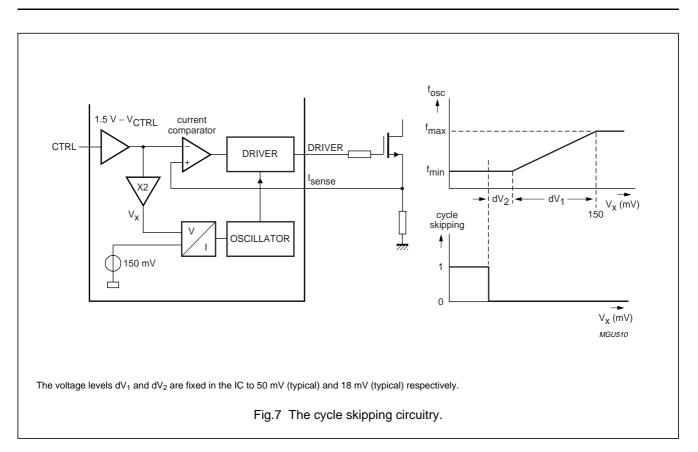
At very low power levels, a cycle skipping mode will be activated. A high control voltage will reduce the switching frequency to a minimum of 25 kHz. If the voltage on the control pin is raised even more, switch-on of the external power MOSFET will be inhibited until the voltage on the control pin has dropped to a lower value again (see Fig.7).

For system accuracy, it is not the absolute voltage on the control pin that will trigger the cycle skipping mode, but a signal derived from the internal VCO will be used.

Remark 1: If the no-load requirement of the system is such that the output voltage can be regulated to its intended level at a switching frequency of 25 kHz or above, the cycle skipping mode will not be activated.

Remark 2: As switching will stop when the voltage on the control pin is raised above a certain level, the burst mode has to be activated by a microcontroller or any other circuit sending a 30  $\mu$ s, 16 mA pulse to the control input (pin CTRL) of the IC.

### TEA1533P; TEA1533AP



### Demagnetization

The system will be in discontinuous conduction mode all the time. The oscillator will not start a new primary stroke until the secondary stroke has ended.

Demagnetization features a cycle-by-cycle output short-circuit protection by immediately lowering the frequency (longer off-time), thereby reducing the power level.

Demagnetization recognition is suppressed during the first  $t_{suppr}$  time. This suppression may be necessary in applications where the transformer has a large leakage inductance, at low output voltages and at start-up.

If pin DEM is open-circuit or not connected, a fault condition is assumed and the converter will stop operating immediately. Operation will recommence as soon as the fault condition is removed.

If pin DEM is shorted to ground, again a fault condition is assumed and the converter will stop operating after the first stroke. The converter will subsequently enter the safe restart mode. This situation will persist until the short-circuit is removed.

### Minimum and maximum 'on-time'

The minimum 'on-time' of the SMPS is determined by the Leading Edge Blanking (LEB) time. The IC limits the 'on-time' to 50  $\mu$ s. When the system desires an 'on-time' longer than 50  $\mu$ s, a fault condition is assumed (e.g. removed C<sub>i</sub> in Fig.11), the IC will stop switching and enter the safe restart mode.

### **OverVoltage Protection (OVP)**

An OVP mode is implemented in the GreenChip series. This works for the TEA1533 by sensing the auxiliary voltage via the current flowing into pin DEM during the secondary stroke. The auxiliary winding voltage is a well-defined replica of the output voltage. Any voltage spikes are averaged by an internal filter.

If the output voltage exceeds the OVP trip level, an internal counter starts counting subsequent OVP events. The counter has been added to prevent incorrect OVP detections which might occur during ESD or lightning events. If the output voltage exceeds the OVP trip level a few times and not again in a subsequent cycle, the internal counter will count down with twice the speed compared with counting-up. However, when typical 10 cycles of subsequent OVP events are detected, the IC assumes a true OVP and the OVP circuit switches the power MOSFET off. Next, the controller waits until the UVLO level is reached on pin  $V_{CC}$ . When  $V_{CC}$  drops to UVLO, capacitor  $C_{VCC}$  will be recharged to the  $V_{start}$  level.

Regarding the TEA1533P, this IC will not start switching again. Subsequently,  $V_{CC}$  will drop again to the UVLO level, etc. Operation only recommences when the  $V_{CC}$  voltage drops below a level of approximately 4.5 V (practically when  $V_{mains}$  has been disconnected for a short period).

Regarding the TEA1533AP, switching starts again (safe restart mode) when the  $V_{start}$  level is reached. This process is repeated as long as the OVP condition exists.

The output voltage V<sub>o(OVP)</sub> at which the OVP function trips, can be set by the demagnetization resistor,  $R_{DEM}$ :

$$\begin{split} V_{o(OVP)} &= \\ \frac{N_s}{N_{aux}} \{ I_{(OVP)(DEM)} \times R_{DEM} + V_{clamp(DEM)(pos)} \} \end{split}$$

where  $N_{s}$  is the number of secondary turns and  $N_{aux}$  is the number of auxiliary turns of the transformer.

Current I<sub>(OVP)(DEM)</sub> is internally trimmed.

The value of  $R_{DEM}$  can be adjusted to the turns ratio of the transformer, thus making an accurate OVP possible.

### TEA1533P; TEA1533AP

### Valley switching

A new cycle starts when the power MOSFET is switched on (see Fig.8). After the 'on-time' (which is determined by the 'sense' voltage and the internal control voltage), the switch is opened and the secondary stroke starts. After the secondary stroke, the drain voltage shows an oscillation

with a frequency of approximately  $\frac{1}{2\times\pi\times\sqrt{(L_p\times C_d)}}$ 

where  $L_p$  is the primary self inductance of the transformer and  $C_d$  is the capacitance on the drain node.

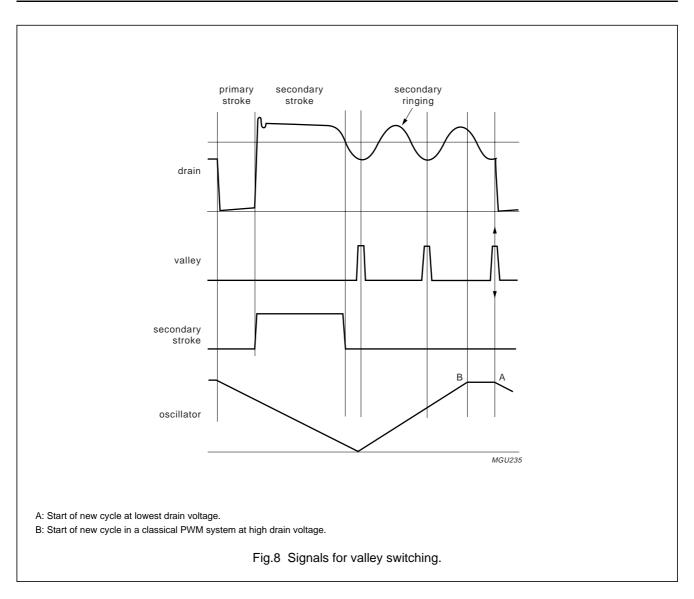
As soon as the oscillator voltage is high again and the secondary stroke has ended, the circuit waits for the lowest drain voltage before starting a new primary stroke. This method is called valley detection. Figure 8 shows the drain voltage together with the valley signal, the signal indicating the secondary stroke and the oscillator signal.

In an optimum design, the reflected secondary voltage on the primary side will force the drain voltage to zero. Thus, zero voltage switching is very possible, preventing large

capacitive switching losses 
$$\left(P = \frac{1}{2} \times C \times V^2 \times f\right)$$
 and

allowing high frequency operation, which results in small and cost effective inductors.

### TEA1533P; TEA1533AP



### **OverCurrent Protection (OCP)**

The cycle-by-cycle peak drain current limit circuit uses the external source resistor to measure the current accurately. This allows optimum size determination of the transformer core (cost issue). The circuit is activated after the leading edge blanking time,  $t_{leb}$ . The OCP circuit limits the 'sense' voltage to an internal level.

### **OverPower Protection (OPP)**

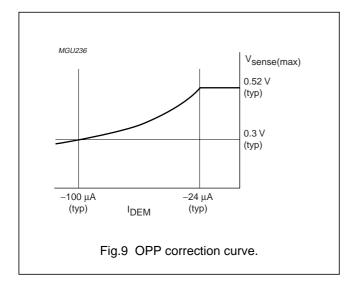
During the primary stroke, the rectified mains input voltage is measured by sensing the current drawn from pin DEM. This current is dependent on the mains voltage, according

to the following formula: 
$$I_{DEM} \approx \frac{V_{aux}}{R_{DEM}} \approx \frac{N \times V_{mains}}{R_{DEM}}$$

where: 
$$N = \frac{N_{aux}}{N_{p}}$$

The current information is used to adjust the peak drain current, which is measured via pin  $I_{sense}$ . The internal compensation is such that an almost mains independent maximum output power can be realized.

The OPP curve is given in Fig.9.



### Short winding protection

After the leading edge blanking time, the short winding protection circuit is activated. If the 'sense' voltage exceeds the short winding protection voltage  $V_{swp}$ , the converter will stop switching. Once  $V_{CC}$  drops below the UVLO level, capacitor  $C_{VCC}$  will be recharged and the supply will restart again. This cycle will be repeated until the short-circuit is removed (safe restart mode).

The short winding protection will also protect in case of a secondary diode short-circuit.

### **OverTemperature Protection (OTP)**

An accurate temperature protection is provided in the circuit. When the junction temperature exceeds the thermal shutdown temperature, the IC will stop switching. When  $V_{CC}$  drops to UVLO, capacitor  $C_{VCC}$  will be recharged to the  $V_{start}$  level.

Regarding the TEA1533P, this IC will not start switching again. Subsequently,  $V_{CC}$  will drop again to the UVLO level, etc. Operation only recommences when the  $V_{CC}$  voltage drops below a level of approximately 4.5 V (practically when the  $V_{mains}$  has been disconnected for a short period).

Regarding the TEA1533AP, when the  $V_{start}$  level is reached, switching starts again (safe restart mode). This process is repeated as long as the OTP condition exists.

### TEA1533P; TEA1533AP

### **Control pin protection**

If pin CTRL is open-circuit or not connected, a fault condition is assumed and the converter will stop switching. Operation will recommence as soon as the fault condition is removed.

### Burst mode standby

Pin CTRL is also used to implement the burst mode standby. In burst mode standby, the power supply enters a special low dissipation state. Figure 11 shows a flyback converter using the burst mode standby function. The system enters burst mode standby when the microcontroller activates NPN transistor T1 on the secondary side.

When the voltage on  $C_{micro}$  exceeds a certain voltage measured by the microcontroller, the opto-coupler is activated by T1, sending a large current signal to pin CTRL. In response to this signal, the IC stops switching and enters a 'hiccup' mode. This burst activation signal should be present for longer than the 'burst blank' period (typically 30  $\mu$ s): the blanking time prevents false burst triggering due to spikes. Figure 12 shows the burst mode standby signals. The hiccup mode during burst mode at safe restart during a system fault condition (e.g. output short-circuit). The power is reduced during soft restart mode.

Burst mode standby operation continues until the microcontroller stops activating transistor T1. The system then enters the start-up sequence and begins normal switching behaviour.

$$I_{burstmode} = \frac{V_{th}}{R_{CTRL}} + I_{th(on)}$$

### Soft start-up

To prevent transformer rattle during hiccup, the transformer peak current is slowly increased by the soft start function. This can be achieved by inserting a resistor and a capacitor between pin  $I_{sense}$  and the sense resistor (see Fig.10). An internal current source charges the capacitor to V =  $I_{SS} \times R_{SS}$ , with a maximum of approximately 0.5 V.

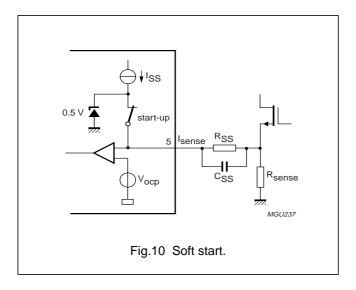
The start level and the time constant of the increasing primary current level can be adjusted externally by changing the values of  $R_{SS}$  and  $C_{SS}$ .

$$I_{primary(max)} = \frac{V_{ocp} - (I_{SS} \times R_{SS})}{R_{sense}}$$

 $\tau = R_{SS} \times C_{SS}$ 

The charging current I<sub>SS</sub> will flow as long as the voltage on pin I<sub>sense</sub> is below approximately 0.5 V. If the voltage on pin I<sub>sense</sub> exceeds 0.5 V, the soft start current source will start limiting the current I<sub>SS</sub>. At the V<sub>CC(start)</sub> level, the I<sub>SS</sub> current source is completely switched off.

Since the soft start current  $I_{SS}$  is subtracted from pin  $V_{CC}$  charging current, the  $R_{SS}$  value will affect the  $V_{CC}$  charging current level by a maximum of 60  $\mu$ A (typical value).



### Driver

The driver circuit to the gate of the power MOSFET has a current sourcing capability of 170 mA typical and a current sink capability of 700 mA typical. This permits fast turn-on and turn-off of the power MOSFET for efficient operation.

TEA1533P; TEA1533AP

A low driver source current has been chosen to limit the  $\Delta V/\Delta t$  at switch-on. This reduces Electro Magnetic Interference (EMI) and also limits the current spikes across  $R_{sense}.$ 

### TEA1533P; TEA1533AP

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); note 1.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Voltages					
V <sub>CC</sub>	supply voltage	continuous	-0.4	+20	V
V <sub>CTRL</sub>	voltage on pin CTRL		-0.4	+5	V
V <sub>DEM</sub>	voltage on pin DEM	current limited	-0.4	_	V
V <sub>sense</sub>	voltage on pin I <sub>sense</sub>	current limited	-0.4	_	V
V <sub>DRAIN</sub>	voltage on pin DRAIN		-0.4	+650	V
Currents			·	ł	·
I <sub>CTRL</sub>	current on pin CTRL	d < 10%	-	50	mA
I <sub>DEM</sub>	current on pin DEM		-250	+250	μA
Isense	current on pin I <sub>sense</sub>		-1	+10	mA
I <sub>DRIVER</sub>	current on pin DRIVER	d < 10%	-0.8	+2	A
I <sub>DRAIN</sub>	current on pin DRAIN		-	5	mA
General					•
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> < 70 °C	-	0.75	W
T <sub>stg</sub>	storage temperature		-55	+150	°C
Tj	operating junction temperature		-20	+145	°C
V <sub>esd</sub>	electrostatic discharge voltage				
	pins 1 to 6	HBM class 1; note 2	-	2000	V
	pin DRAIN	HBM class 1; note 2	_	1500	V
	any pin	note 3	_	400	V

### Notes

- All voltages are measured with respect to ground; positive currents flow into the IC; pin V<sub>CC</sub> may not be current driven. The voltage ratings are valid provided other ratings are not violated; current ratings are valid provided the maximum power rating is not violated.
- 2. Equivalent to discharging a 100 pF capacitor through a 1.5 k $\Omega$  resistor.
- 3. Equivalent to discharging a 200 pF capacitor through a 0.75  $\mu$ H coil and a 10  $\Omega$  resistor.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air; note 1	100	K/W

### Note

1. With pin GND connected to sufficient copper area on the printed-circuit board.

### QUALITY SPECIFICATION

In accordance with 'SNW-FQ-611-D'.

### TEA1533P; TEA1533AP

### CHARACTERISTICS

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 15 V; all voltages are measured with respect to ground; currents are positive when flowing into the IC; unless otherwise specified.

PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
nt source (pin DRAIN)	1	1		1		
supply current drawn from	V <sub>CC</sub> = 0 V; V <sub>DRAIN</sub> > 100 V	1.0	1.2	1.4	mA	
pin DRAIN	with auxiliary supply; V <sub>DRAIN</sub> > 100 V	_	100	300	μA	
breakdown voltage		650	_	-	V	
mains-dependent operation enabling level		60	_	100	V	
e management (pin V <sub>CC</sub> )						
start-up voltage on V <sub>CC</sub>		10.3	11	11.7	V	
undervoltage lock-out on $V_{CC}$		8.1	8.7	9.3	V	
hysteresis voltage on V <sub>CC</sub>	V <sub>CC(start)</sub> – V <sub>CC(UVLO)</sub>	2.0	2.3	2.6	V	
pin V <sub>CC</sub> charging current, high	V <sub>DRAIN</sub> > 100 V; V <sub>CC</sub> < 3 V	-1.2	-1	-0.8	mA	
pin $V_{CC}$ charging current, low	$V_{DRAIN} > 100 V;$ 3 V < V <sub>CC</sub> < V <sub>CC(UVLO)</sub>	-1.2	-0.75	-0.45	mA	
pin V <sub>CC</sub> restart current	V <sub>DRAIN</sub> > 100 V; V <sub>CC(UVLO)</sub> < V <sub>CC</sub> < V <sub>CC(start)</sub>	-650	-550	-450	μA	
supply current under normal operation	no load on pin DRIVER	1.1	1.3	1.5	mA	
supply current while not switching		_	0.85	_	mA	
on management (pin DEM)	•			·		
demagnetization comparator threshold voltage on pin DEM		50	100	150	mV	
protection current on pin DEM	V <sub>DEM</sub> = 50 mV	-50 <sup>(1)</sup>	_	-10	nA	
negative clamp voltage on pin DEM	I <sub>DEM</sub> = -150 μA	-0.5	-0.25	-0.05	V	
positive clamp voltage on pin DEM	I <sub>DEM</sub> = 250 μA	0.5	0.7	0.9	V	
suppression of transformer ringing at start of secondary stroke		1.1	1.5	1.9	μs	
odulator	•	•				
minimum on-time		_	t <sub>leb</sub>	-	ns	
maximum on-time	latched	40	50	60	μs	
oscillator low fixed frequency	V <sub>CTRL</sub> > 1.5 V	20	25	30	kHz	
oscillator high fixed frequency	V <sub>CTRL</sub> < 1 V	145	175	205	kHz	
peak voltage on pin I <sub>sense</sub> , where frequency reduction starts	see Figs 6 and 7	-	VCO <sub>1</sub>	-	mV	
	Imply current of the product of the	Image: Supply current drawn from pin DRAIN $V_{CC} = 0 \text{ V}; \text{ V}_{DRAIN} > 100 \text{ V}$ with auxiliary supply; $\text{V}_{DRAIN} > 100 \text{ V}$ breakdown voltage	Image: supply current drawn from pin DRAIN $V_{CC} = 0 \text{ V}; V_{DRAIN} > 100 \text{ V}$ 1.0supply current drawn from pin DRAIN $V_{CC} = 0 \text{ V}; V_{DRAIN} > 100 \text{ V}$ 1.0breakdown voltage $With$ auxiliary supply; $V_{DRAIN} > 100 \text{ V}$ 650mains-dependent operation enabling level600management (pin V <sub>CC</sub> )start-up voltage on V <sub>CC</sub> 10.3start-up voltage lock-out on V <sub>CC</sub> $V_{CC(start)} - V_{CC(UVLO)}$ 2.0pin V <sub>CC</sub> charging current, high $V_{DRAIN} > 100 \text{ V}; V_{CC} < 3 \text{ V} - 1.2$ pin V <sub>CC</sub> charging current, low $V_{DRAIN} > 100 \text{ V}; V_{CC} < 3 \text{ V} - 1.2$ pin V <sub>CC</sub> charging current, low $V_{DRAIN} > 100 \text{ V}; V_{CC} < 3 \text{ V} - 1.2$ pin V <sub>CC</sub> crestart current $V_{DRAIN} > 100 \text{ V}; V_{CC} < 5.2$ supply current under normal operationno load on pin DRIVERsupply current while not switching-on management (pin DEM)for $V_{DEM} = 50 \text{ mV}$ demagnetization comparator threshold voltage on pin DEM $I_{DEM} = -150 \mu\text{A}$ positive clamp voltage on pin DEM $I_{DEM} = 250 \mu\text{A}$ 0.5suppression of transformer ringing at start of secondary stroke1.1oscillator low fixed frequency $V_{CTRL} > 1.5 V$ 20oscillator high fixed frequency $V_{CTRL} < 1.4 V$ 145peak voltage on pin Isense, wheresee Figs 6 and 7-	Intro source (pin DRAIN)supply current drawn from pin DRAIN $V_{CC} = 0 V; V_{DRAIN} > 100 V$ 1.01.2with auxiliary supply; $V_{DRAIN} > 100 V$ -100breakdown voltage650-mains-dependent operation enabling level600- <b>a management (pin V_{CC})</b> 110.311start-up voltage on V_{CC}10.311undervoltage lock-out on V_{CC}8.18.7hysteresis voltage on V_{CC}V_C((start) - V_{CC(UVLO)})2.02.3pin V_{CC} charging current, highV_DRAIN > 100 V; V_CC < 3 V	Introsence (pin DRAIN)   Supply current drawn from pin DRAIN V <sub>CC</sub> = 0 V; V <sub>DRAIN</sub> > 100 V 1.0 1.2 1.4   supply current drawn from pin DRAIN V <sub>CC</sub> = 0 V; V <sub>DRAIN</sub> > 100 V 1.0 1.2 1.4   breakdown voltage 650 - - 100 300   breakdown voltage on v <sub>CC</sub> 650 -   amangement (pin V <sub>CC</sub> )   start-up voltage on V <sub>CC</sub> V <sub>CC(start</sub> ) - V <sub>CC(UVLO</sub> ) 2.0 2.3 2.6   pin V <sub>CC</sub> charging current, high V <sub>DRAIN</sub> > 100 V; V <sub>CC</sub> < 3 V - - -   pin V <sub>CC</sub> charging current, high V <sub>DRAIN</sub> > 100 V; V <sub>CC</sub> < 3 V - -   pin V <sub>CC</sub> charging current, high V <sub>DRAIN</sub> > 100 V; V <sub>CC</sub> < 3 V - -   pin V <sub>CC</sub> charging current, high V <sub>DRAIN</sub> > 100 V; V <sub>CC</sub> < 3 V - -   gupply current under normal  - <th colsp<="" td=""></th>	

### TEA1533P; TEA1533AP

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>vco(max)</sub>	peak voltage on pin $I_{sense}$ , where the frequency is equal to $f_{osc(I)}$		_	VCO <sub>1</sub> – 25	-	mV
Duty cycle co	ntrol (pin CTRL)					•
V <sub>CTRL(min)</sub>	minimum voltage on pin CTRL for maximum duty cycle		_	1.0	-	V
V <sub>CTRL(max)</sub>	maximum voltage on pin CTRL for minimum duty cycle		-	1.5	-	V
Iprot(CTRL)	protection current on pin CTRL	V <sub>CTRL</sub> = 1.5 V	-1 <sup>(1)</sup>	-0.8	-0.5	μA
Burst mode s	tandby (pin CTRL)					
V <sub>th(burst)(on)</sub>	burst mode standby active threshold voltage	I <sub>burst</sub> = 6 mA	3.3	3.8	4.3	V
I <sub>th(burst)(on)</sub>	burst mode standby active current		16	-	-	mA
Ith(burst)(off)	burst mode standby inactive current		-	-	6	mA
t <sub>(burst-blank)</sub>	burst mode standby blanking time		25	30	35	μs
Valley switch	(pin DRAIN)					
$\Delta V / \Delta t_{valley}$	valley recognition voltage change		-85	-	+85	V/µs
t <sub>valley</sub> -swon	delay from valley recognition to switch-on		-	150 <sup>(1)</sup>	-	ns
Overcurrent a	nd short winding protection (pin $I_s$	ense)				
V <sub>sense(max)</sub>	maximum source voltage OCP	$\Delta V/\Delta t = 0.1 V/\mu s$	0.48	0.52	0.56	V
t <sub>PD</sub>	propagating delay from detecting V <sub>sense(max)</sub> to switch-off	$\Delta V/\Delta t = 0.5 V/\mu s$	-	140	185	ns
V <sub>swp</sub>	short winding protection voltage		0.83	0.88	0.96	V
t <sub>leb</sub>	blanking time for current and short winding protection		300	370	440	ns
I <sub>SS</sub>	soft start current	V <sub>sense</sub> < 0.5 V	45	60	75	μΑ
Overvoltage p	protection (pin DEM)					
I <sub>OVP(DEM)</sub>	OVP level on pin DEM	set by resistor R <sub>DEM</sub> , see Section "OverVoltage Protection (OVP)"	54	60	66	μA
Overpower pr	otection (pin DEM)					
I <sub>OPP(DEM)</sub>	OPP current on pin DEM to start OPP correction	set by resistor R <sub>DEM</sub> , see Section "OverPower Protection (OPP)"	-	-24	-	μΑ
I <sub>OPP50%</sub> (DEM)	OPP current on pin DEM, where maximum source voltage is limited to 0.3 V		-	-100	-	μΑ

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Driver (pin DR	IVER)					
I <sub>source</sub>	source current capability of driver	V <sub>CC</sub> = 9.5 V; V <sub>DRIVER</sub> = 2 V	-	-170	-88	mA
I <sub>sink</sub>	sink current capability of driver	V <sub>CC</sub> = 9.5 V; V <sub>DRIVER</sub> = 2 V	-	300	-	mA
		V <sub>CC</sub> = 9.5 V; V <sub>DRIVER</sub> = 9.5 V	400	700	-	mA
V <sub>o(max)</sub>	maximum output voltage of the driver	V <sub>CC</sub> > 12 V	-	11.5	12	V
Temperature p	protection					
T <sub>prot(max)</sub>	maximum temperature protection level		130	140	150	°C
T <sub>prot(hys)</sub>	hysteresis for the temperature protection level		-	8(1)	-	°C

Note

1. Guaranteed by design.

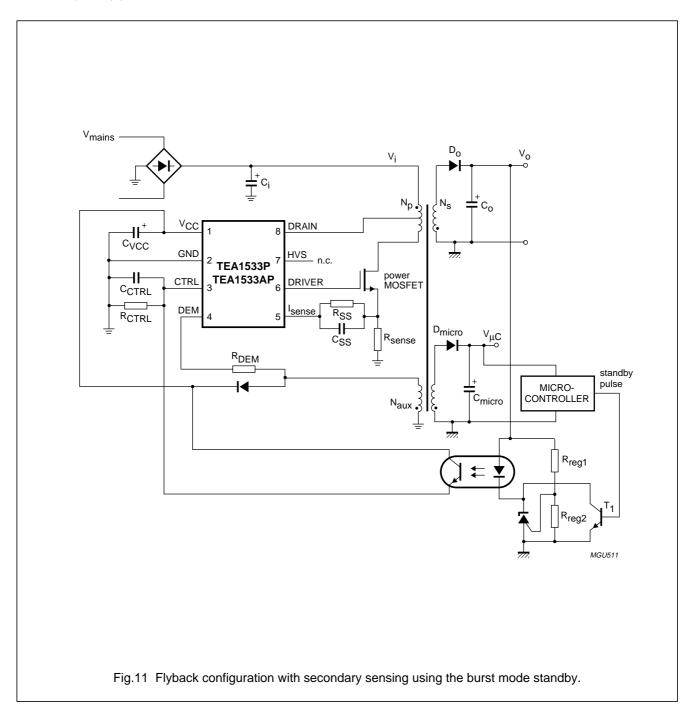
### TEA1533P; TEA1533AP

### **APPLICATION INFORMATION**

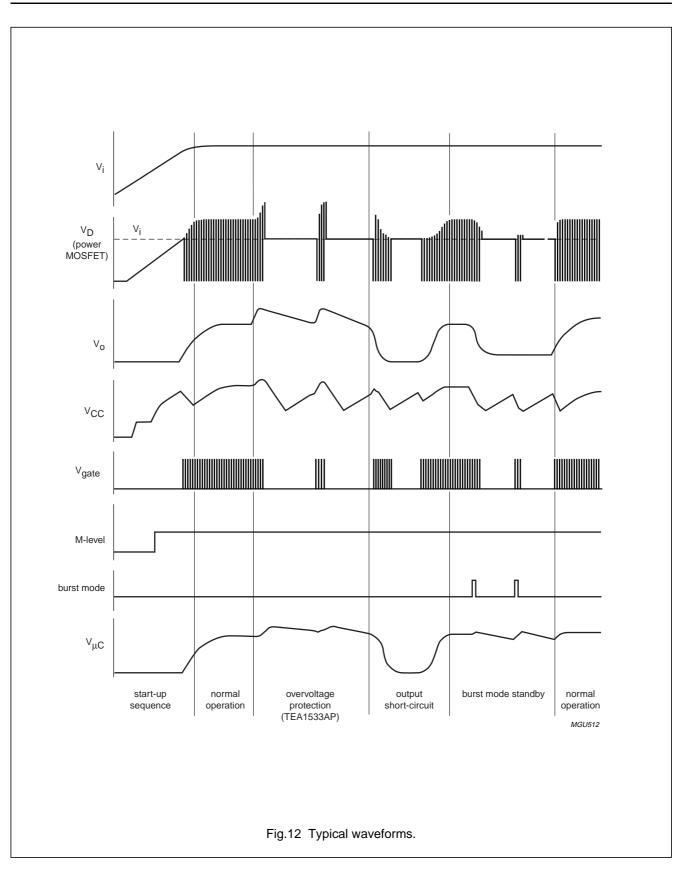
A converter with the TEA1533 consists of an input filter, a transformer with a third winding (auxiliary), and an output stage with a feedback circuit.

Capacitor  $C_{VCC}$  (at pin  $V_{CC}$ ) buffers the supply voltage of the IC, which is powered via the high voltage rectified mains during start-up and via the auxiliary winding during operation.

A sense resistor converts the primary current into a voltage at pin I<sub>sense</sub>. The value of this sense resistor defines the maximum primary peak current.



### TEA1533P; TEA1533AP



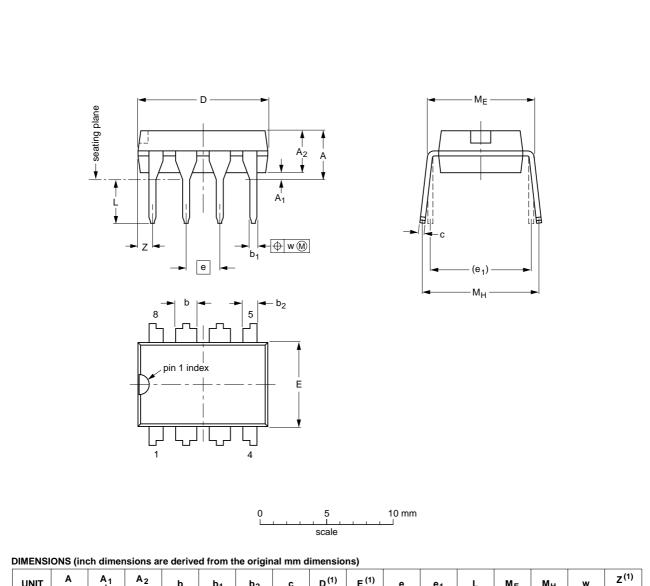
SOT97-1

### GreenChip<sup>TM</sup>II SMPS control IC

### TEA1533P; TEA1533AP

### PACKAGE OUTLINE

DIP8: plastic dual in-line package; 8 leads (300 mil)



	UNIT	max.	min.	max.	b	b <sub>1</sub>	b <sub>2</sub>	C	D(1)	E('')	е	e <sub>1</sub>	L	ME	M <sub>H</sub>	w	max.
	mm	4.2	0.51	3.2	1.73 1.14	0.53 0.38	1.07 0.89	0.36 0.23	9.8 9.2	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	1.15
i	inches	0.17	0.020	0.13	0.068 0.045	0.021 0.015	0.042 0.035	0.014 0.009	0.39 0.36	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.045

### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ	J PRO.		ISSUE DATE	
SOT97-1	050G01	MO-001	SC-504-8			<del>95-02-04</del> 99-12-27	

### SOLDERING

### Introduction to soldering through-hole mount packages

This text gives a brief insight to wave, dip and manual soldering. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

Wave soldering is the preferred method for mounting of through-hole mount IC packages on a printed-circuit board.

### Soldering by dipping or by solder wave

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joints for more than 5 seconds.

The total contact time of successive solder waves must not exceed 5 seconds.

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The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ( $T_{stg(max)}$ ). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

### Manual soldering

Apply the soldering iron (24 V or less) to the lead(s) of the package, either below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300  $^{\circ}$ C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400  $^{\circ}$ C, contact may be up to 5 seconds.

### Suitability of through-hole mount IC packages for dipping and wave soldering methods

PACKAGE	SOLDERING METHOD				
FACKAGE	DIPPING	WAVE			
DBS, DIP, HDIP, SDIP, SIL	suitable	suitable <sup>(1)</sup>			

### Note

1. For SDIP packages, the longitudinal axis must be parallel to the transport direction of the printed-circuit board.

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### DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

### Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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